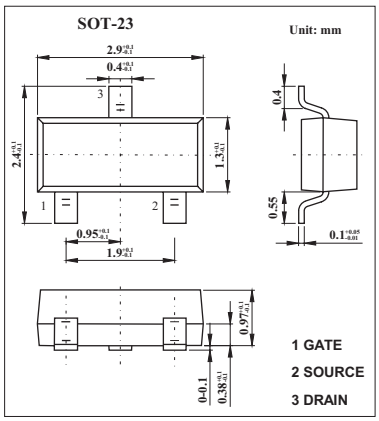
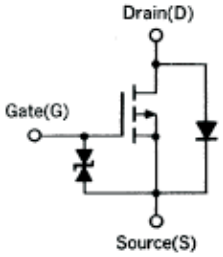
MOS Fied Effect Transistor

2SJ166



Features

- Directly driven by Ics having a 5V poer supply.
- Not necessary to consider dreving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage VGS=0	VDSS	-50	V
Gate to source voltage VDS=0	VGSS	±7.0	V
Drain current (DC)	ID	±100	mA
Drain current(pulse) *	ID	±200	mA
Total power dissipation	PT	200	mW
Channel temperature	Tch	150	℃
Storage temperature	Tstg	-55 to +150	℃

* PW ⩽ 10 ms; d ⩽ 50%.

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	IDSS	VDS=-50V,VGS=0			-10	μA
Gate leakage current	IGSS	VGS=±7.0V,VDS=0			±1.0	μA
Gate cut-off voltage	VGS(off)	VDS=-5.0V,ID=-1.0μA	-1.0	-2.1	-3.0	V
Forward transfer admittance	|Yfs|	VDS=-5.0V,ID=-20mA	30	50		ms
Drain to source on-state resistance	RDS(on)	VGS=-4.0V,ID=-20mA		18	50	Ω
Input capacitance	Ciss	VDS=-5.0V,VGS=0,f=1Mhz		18		pF
Output capacitance	Coss			11		pF
Reverse transfer capacitance	Crss			3		pF
Turn-on delay time	td(on)	VGS(on)=-5.0V,RG=10Ω,VDD=-5.0V,ID=-20mA RL=250Ω		40		ns
Rise time	tr			58		ns
Turn-off delay time	td(off)			62		ns
Fall time	tf			62		ns

Marking

Marking	H11